

SA100 SERIES

SURGE ARRESTORS

FEATURES

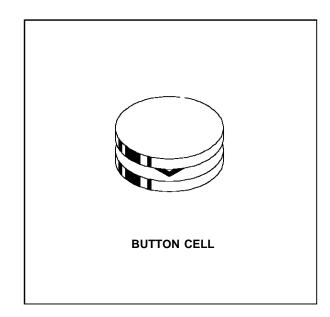
- SOLID STATE SURGE ARRESTOR
- VOLTAGE RANGE = 200 V TO 265 V
- TIGHT VOLTAGE TOLERANCE
- FAST RESPONSE TIME
- VERY LOW AND STABLE LEAKAGE CURRENT
- REPETITIVE SURGE CAPABILITY Ipp = 100 A, 10/1000 μs
- FAIL-SAFE WHEN DESTROYED

DESCRIPTION

Bidirectional device used for primary protection in telecom equipments.

Providing long service life, and adapted for sensitive electronic equipments protection.

If destroyed the component will continue to guarantee a protection with a permanent short circuit, meaning "fail save criteria". This particular behaviour will also allow an easy failure detection on the line.



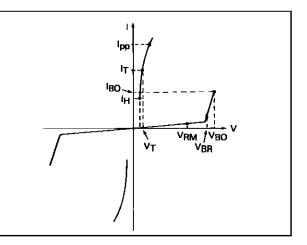
	ABSOLUTE RATINGS	(limiting valu	ues) - 40°C <	: T _{amb} < +80°C
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Symbol	Parameter	Value	Unit	
IPP	Peak Pulse Current.	10/1000 μs	100	A
		8/20 μs	200	A
	Fail Save Criteria.	8/20 μs	10	kA
I _{TSM}	Non Repetitive Surge Peak on-state Current	60 Hz	30	A
	One cycle.	50Hz	25	A
	Non Repetitive Surge Peak on-state Current	1s	14	A
	F = 50 Hz.	2s	10	A
dv/dt	Critical Rate of Rise of on-state Voltage.	67% V _{BR}	10	kV/μs
ΤL	Maximum Lead Temperature to Soldering During	250	°C	

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ELECTRICAL CHARACTERISTICS

Symbol	Parameter						
V _{RM}	Stand-off Voltage						
V BR	Breakdown Voltage						
V _{BO}	Breakover Voltage						
Ι _Η	Holding Current						
V _T	On-state Voltage						
IBO	Breakover Current						



Туре	I _{RM} @ V _{RM} V _{BR} @		@ IR	VBO	VBO	VBO	IBO	lΗ	VT	С	
	max		min.		max.	max.	max.	min.	min.	max.	max.
					note 1	note 2	note 3	note 1	note 1	note 4	note 5
	(μΑ)	(V)	(V)	(mA)	(V)	(V)	(V)	(mA)	(mA)	(V)	pF
SA100-230 SA100-300	10 10	170 225	200 265	1 1	265 400	350 400	350 400	200 200	260 260	3.5 3.5	200 200

All parameters tested at 25°C, except where indicated.

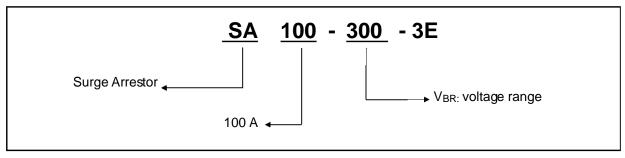
Note 1 : See the reference test circuit for IH,IBO and VBO parameters Note 2 : $V_{RISE} = 100V/\mu s$.

Note 3 : $V_{RISE} = 1KV/\mu s$, di/dt < 10A/ μs , IPP= 10A.

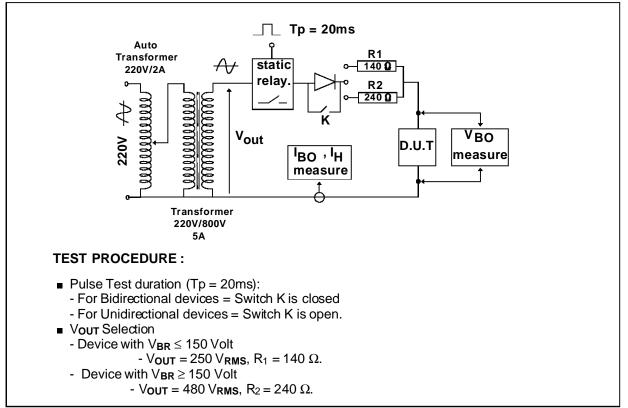
Note 4 : Square pulse, $T_P = 500 \,\mu s$, $I_T = 5 \,A$.

Note 5: $V_R = 0 V, F = 1 MHz$.

ORDER CODE

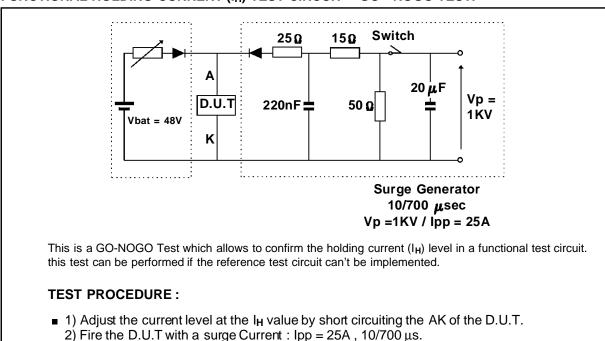


Product Availability is Submitted to Restricted Conditions- Consult Factory.



REFERENCE TEST CIRCUIT FOR $I_{H},\,I_{BO}$ and V_{BO} parameters :

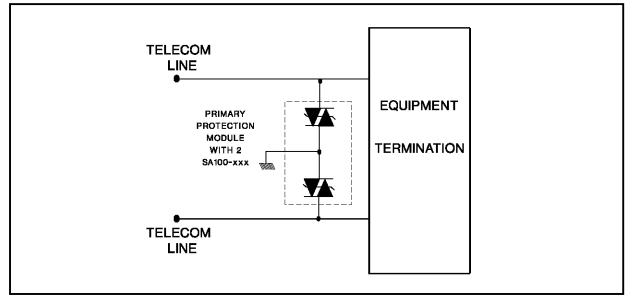
FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT = GO - NOGO TEST.



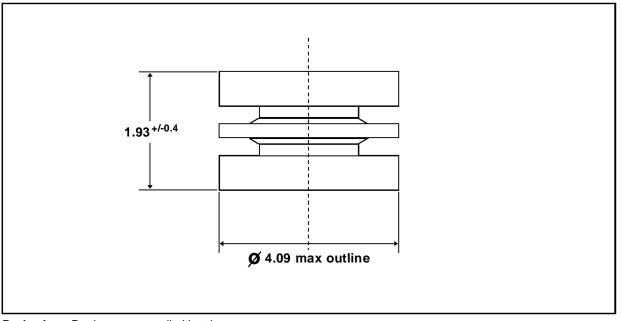
3) The D.U.T will come back to the OFF-State within a duration of 50 ms max.

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APPLICATION DIAGRAM



MECHANICAL DATA BUTTON CELL (Millimeters)



Packaging : Products are supplied in tubes.



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